

1.65V – 3.6V, 1x Micro Deviation EMI Reduction IC

Features

- FCC approved method of EMI attenuation
- Proprietary "SaΦic™" technology, a non-PLL phase controlled active EMI management architecture
- Generates a 1X low EMI Phase Modulated replication of the input signal.
- Vdd 1.65V 2.0V 10 MHz to 33 MHz
- Vdd 2.5V 3.6V 10 MHz to 55 MHz
- Multiple Deviation Selections
- Minimum frequency deviation selection capability
- Power Down Mode
- 8-pin WDFN package
- Supports automotive reliability standard: AEC-Q100 Grade 1 and Grade 2 certified

Product Description

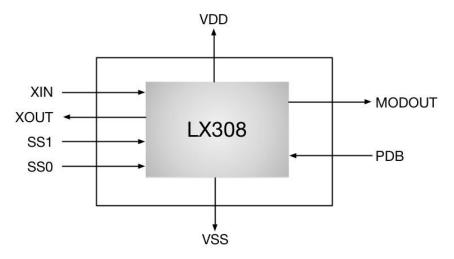
The LX308 is a versatile 1x Active EMI management IC designed to provide system wide reduction of Electromagnetic Interference (EMI) and Radio Frequency Interference (RFI) from clock and data sources. The LX308 allows significant system cost savings by reducing the number of circuit board layers, ferrite beads, shielding and other passive components that are traditionally required to pass EMI regulations.

The LX30x family of mobile active EMI management ICs is unique in it's design and is based on LFC's proprietary "SaΦic" phase controlled Active EMI management technology. This allows operation on aperiodic as well periodic signals. By the precise placement of the edges of the reconstructed input signal, the peak energy of the output is distributed over a wider and controlled energy band thereby significantly lowering system EMI compared to the typical narrow band signal produced by oscillators and most frequency generators. The LX308 has an input frequency range of 10 MHz to 55MHz over a wide voltage range of 1.65V to 3.6V. The device can be placed in a "power save mode" by setting the PDB pin to GND where in it draws typically 40uA and also sets the MODOUT pin to a High-Z state. The device has two "deviation control pins" SS1 and SS0 to allow flexibility and optimization of both EMI compliance as well as in system design. The device is available in an 8-pin WDFN package.

Applications

The LX308 is targeted towards mobile platforms such as cell phones, MIDs, notebooks and other "power and space" sensitive applications.

Block Diagram

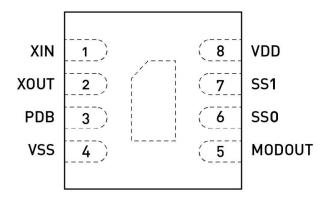


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Pin Configuration



Pin Description

Pin#	Pin Name	Туре	Description
1	XIN	I	Crystal Oscillator Input.
2	XOUT	0	Crystal Oscillator Output.
3	PDB	I	Power Down pin. Active Low. Forces MODOUT to High-Z. Internal Pull-Up resistor.
4	VSS	Р	System ground reference input.
5	MODOUT	0	1X phase modulated buffered output.
6	SS0	I	Deviation Control Pin (refer Functionality Table) Internal Pull-Up Resistor. Recommend external Pull-Down Resistor 0Ω .
7	SS1	I	Deviation Control Pin (refer Functionality Table) Internal Pull-Down Resistor. Recommend external Pull-Up Resistor 0Ω .
8	VDD	0	System Power Supply pin.

Operating Conditions

Parameter	Description	Min	Мах	Unit
V _{DD (3.3V)}	Supply Voltage	1.65	3.6	V
T _A	Operating Temperature (Ambient Temperature)	-40	+125	°C
CL	Load Capacitance		20	pF
C _{IN}	Input Capacitance		5	pF

Note: Please refer to ordering information for TA

Absolute Maximum Rating

Symbol	Parameter	Rating	Unit				
Vin	Voltage on any pin with respect to Ground	-0.5 to +4.6	V				
Tstg	Storage temperature -65 to +125 °C						
Ts	Max. Soldering Temperature (10 sec)	260	°C				
TJ	Junction Temperature	150	°C				
T _{DV}	Static Discharge Voltage (As per JEDEC STD22- A114-B)		KV				
	Note: These are stress ratings only and are not implied nor guaranteed for functional use. Exposure to absolute maximum ratings for prolonged periods of time may affect device reliability.						

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Functional Table

	Freq. Erec		Deviation (%)								
VDD(V)	Range	Freq. (MHz)	SS1	SS0	SS1	SS0	SS1	SS0	SS1	SS0	
	(MHz)	()	0	0	0	1	1	0	1	1	
1.8		12	±0.	±0.05		.06	±0.06		±0.10		
1.8	10~33	24	±0.	±0.07		±0.10		±0.11		±0.19	
1.8	10~33	27	±0.07		±0.12		±0.12		±0.21		
1.8		33	±0.	08	±0.15		±0.13		±0.24		
3.3		12	/	,	/		1		±0.05		
3.3	40 55	24	±0.	.04	±0.06		±0.06		±0.09		
3.3	10~55	48	±0.	.04	±0	.06	±0.07		±0.12		
3.3		54	±0.	04	±0.07		±0.07		±0.10		

Note: Specified at VDD 1.8V/3.3V and room temperature. Frequency deviation can vary over voltage and temperature by +/-20%

DC Electrical Characteristics (3.3V +/-0.3V)

Parameter	Description	Test Conditions		Min	Тур	Max	Unit
V _{DD}	Supply Voltage			3.0	3.3	3.6	V
VIH	Input HIGH Voltage			0.66*Vdd			V
VIL	Input LOW Voltage					0.33*Vdd	V
Ін	Input HIGH Current (pin 3/6/7)	VIN = VDD				10	μA
lı∟	Input LOW Current (pin 3/6/7)	VIN = 0V				10	μA
V _{он}	Output HIGH Voltage	IOH = -8r	nA	0.75*Vdd			V
V _{OL}	Output LOW Voltage	IOL = +8r	nA			0.25*Vdd	V
Icc	Static Supply Current	PDB = VS	SS		40	50	μA
I _{DD}	Dynamic Supply Current	27 MHZ	Unloaded		7.0	8.0	mA
טטי	(SS1=1,SS0=1)	10pF load			8.0	9.0	
Zo	Output Impedance				25		V

Switching Characteristics (3.3V +/-0.3V)

Parameter	Description	Test Conditions	Min	Тур	Max	Unit
INPUT	Input Frequency		10	24	55	MHz
MODOUT	Output Frequency		10	24	55	
T _d	Duty Cycle 1,2 = $(t_2 / t_1) * 100$	Measured at VDD /2	45	50	55	%
t ₃	Output Rise Time 1,2	Measured between 20% to 80%	0.6	1.5	2.5	nS
t4	Output Fall Time 1,2	Measured between 80% to 20%	0.6	1.5	2.5	nS
tJ	Cycle-to-cycle jitter ²	Unloaded outputs 27 MHz		+/-250		pS

Notes:

1. All parameters specified with 27MHz without loaded outputs and VDD 3.3V

2. Parameter is guaranteed by design and characterization. Not 100% tested in production



DC Electrical Characteristics (1.8V +/-0.15V)

Parameter	Description	Test Conditions		Min	Тур	Max	Unit
V _{DD}	Supply Voltage			1.65	1.8	1.95	V
VIH	Input HIGH Voltage			0.66*Vdd			V
VIL	Input LOW Voltage					0.33*Vdd	V
I _{IH}	Input HIGH Current (pins 3/6/7)	V _{IN} = VDD				10	μA
lı∟	Input LOW Current (pins 3/6/7)	V _{IN} = 0V				10	μA
V _{он}	Output HIGH Voltage	I _{он} = -4m	A	0.75*Vdd			V
V _{OL}	Output LOW Voltage	I _{OL} = +4m	A			0.25*Vdd	V
Icc	Static Supply Current	PDB = VS	SS		20	30	μA
1	Dynamic Supply Current	27 MHz	Unloaded		3.0	4.0	
IDD	(SS1=1,SS0=0)		10pF load		3.5	4.5	mA
Zo	Output Impedance				25		Ω

Switching Characteristics (1.8+/-0.15V)

Parameter	Description	Test Conditions	Min	Тур	Max	Unit
INPUT	Input Frequency		10	24	33	MHz
MODOUT	Output Frequency		10	24	33	IVITIZ
T _d	Duty Cycle 1,2 = $(t_2 / t_1) * 100$	Measured at VDD /2	45	50	55	%
t ₃	Output Rise Time ^{1,2}	Measured between 20% to 80%	1.0	2.0	3.0	nS
t4	Output Fall Time 1,2	Measured between 80% to 20%	1.0	1.8	3.0	nS
tJ	Cycle-to-cycle jitter ²	Unloaded outputs 27 MHz		+/-250		pS

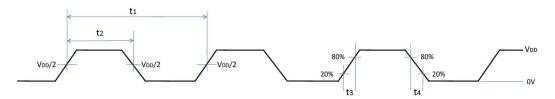
Notes:

1. All parameters specified with 27MHz without loaded outputs and VDD1.8V

2. Parameter is guaranteed by design and characterization. Not 100% tested in production

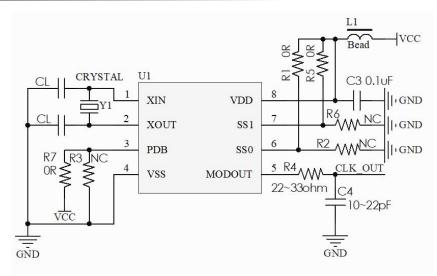


All Outputs Rise/Fall Time

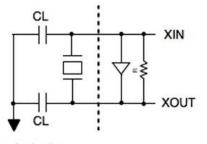


Application Schematic

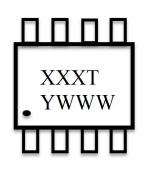




Crystal Oscillator Circuit



Marking Information



XXX: Part NumberT: Temperature GradeY: Year of ProductionWWW: Work Order No.

CL=2x(Cp-Cs)	
Cp: load capacitance of Crystal	
Cs: Stray capacitance (PCB trace + Input cap. of IC)

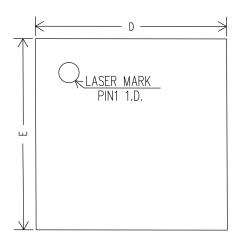
Ordering Information

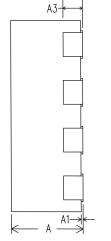
Part Number	Temp. Grade Indicator	Temp Grade	Temp Range	IC Marking	IC Package	Tape & Reel
LX308C	С	Commercial	0°~70°C	308C		4.000 (D
LX308I	1	Industrial	-20°~85°C	3081	2mm x 2mm	
LX308E	E	Automotive AEC Q100 Grade 2	-40°~105°C	308E	8L WDFN	4,000pcs/Reel
LX308A	А	Automotive AEC Q100 Grade 1	-40°~125°C	308A		



Package Dimension

WDFN

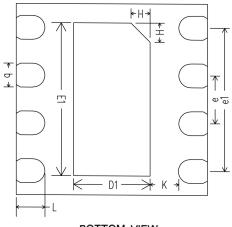




(UNITS OF MEASURE = MILLIMETER					
SYMBOL	MIN	NOM	MAX		
А	0.70	0.75	0.80		
A1	0.00	0.02	0.05		
A3		0.203REF			
В	0.20	0.25	0.30		
D	1.95	2.00	2.05		
E	1.95	2.00	2.05		
D1	0.75	0.80	0.85		
E1	1.55	1.60	1.65		
e	0.40	0.50	0.60		
E1	1.40	1.50	1.60		
н	0.20REF				
К	0.20	0.30	0.40		
L	0.25	0.30	0.35		

COMMON DEMENSIONS





BOTTOM VIEW





SIDE VIEW

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Revision History

Revision Number	Date of Release	Changes
2.1	3/1/2019	 1) Input frequency range 2) AC Characteristics 3) Device Marking Spec 4) Addition of AEC-Q100 Grade 1 & Grade 2
2.2	8/20/2019	1) Add +/- tolerance 0.05mm to package dimension D and E
2.3	11/26/2019	1) Deviation updates
2.4	7/16/2020	1) t ₃ /t ₄ updates
2.5	5/13/2021	1) Update D2, L and E2 package dimension
2.6	9/24/2021	 Deviation updates Static current update PDB pin update
2.7	7/23/2023	 Update the application schematic Update the deviation